

S-Band, GaN/SiC, 50-Ohm RF Power Transistor

2.7 - 3.1GHz | 120 W typ | 50% Efficiency typ | 13dB Gain typ | 32 V | 40ms Pulse Length, 50% Duty Cycle

IGT2731L120 and IGT2731L120S are high power GaN-on-SiC RF power transistors that are fully matched to 50Ω at both the input and output. They supply a minimum of 120W of peak output power, with typically >13dB of gain and 50% efficiency. They operate from a 32V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.



FEATURES

- GaN on SiC HEMT Technology
- Output Power 120W
- Fully matched to 50Ω at both input and output
- 100% RF Tested Under 40ms, 50% duty cycle pulse conditions
- RoHS and REACH Compliant
- IGT2731L120 has a bolt-down flange, IGT2731L120S has an ear-less flange for solder attach only

APPLICATIONS

- S-band Radar Systems

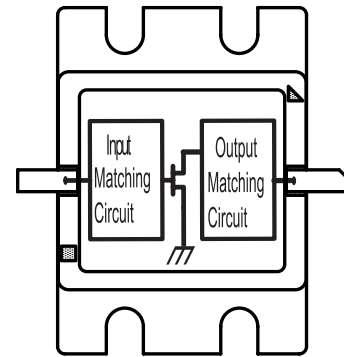


Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated).

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gain	G	10	13	17	dB	$P_{OUT} = 120W$ $f = 2.7, 2.9, 3.1 \text{ GHz}$ 40ms pulse length, 50% duty cycle $V_{DS} = 32V, I_{DS} = 100mA$
Drain Efficiency	η	45	50	75	%	
Pulse Droop	D	-0.8	-0.4	+0.2	dB	
Input Return Loss	IRL	7	10	18	dB	
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 2. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V_p	-4.0	-3.0	-2.5	V	$V_{DS} = 32V, I_{DS} = 2mA$
Quiescent Gate Voltage	V_q		-2.3		V	$V_{DS} = 32V, I_{DS} = 100mA$

Table 3. Absolute Maximum Ratings (Not Simultaneous). Case temperature = 25 °C unless otherwise stated.

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V_{DS}	80	V	
DC Gate-Source Voltage	V_{GS}	-8 to +1.5	V	
DC Drain Current	I_D	24	A	
DC Gate Current	I_G	2.4	mA	
RF Input Power	$P_{RF,IN}$	12	W	
Operating Channel Temperature	T_{CH}	-55 to +225	°C	
Storage Temperature	T_{STG}	-55 to +132	°C	
Soldering Temperature	T_{SOLDER}	260 for 10s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

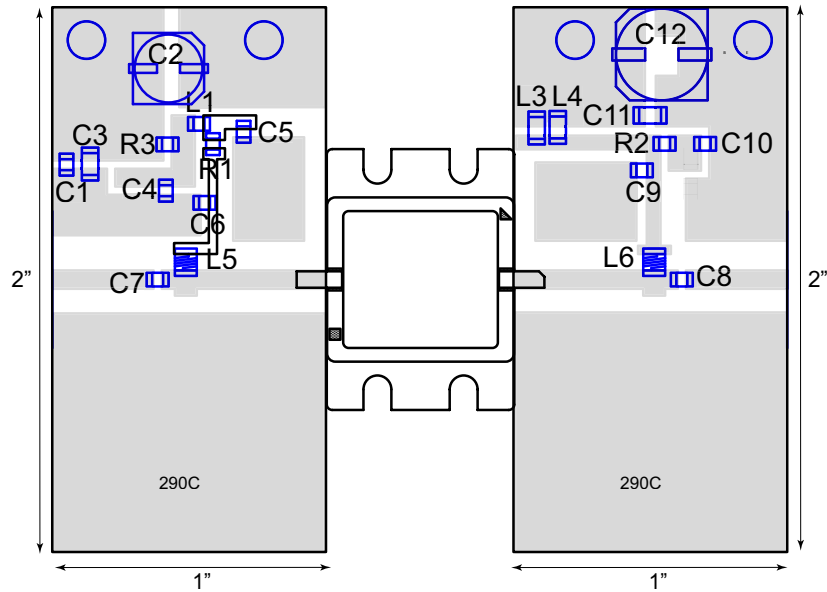
Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	R_{TH}		TBD		°C/W	$P_{DISS} = 120W$ 40ms pulse length, 50% duty cycle $V_{DS} = 32V$

Table 5. Typical RF Electrical Characteristics above Nominal Frequency Range (Case temperature = 30 °C unless otherwise stated).

Frequency (GHz)	Power Output (W)	Gain (dB)	Efficiency (%)	Droop (dB)	Input Return Loss (dB)	Test Conditions
3.2	122	12.9	50.3	-0.22	18	40ms pulse length, 50% duty cycle $V_{DS} = 32V, I_{DS} = 100mA$
	146	12.3	53.4	-0.22	17	
3.3	120	11.7	52.0	-0.21	6.5	
	131	11.3	53.5	-0.21	6.4	

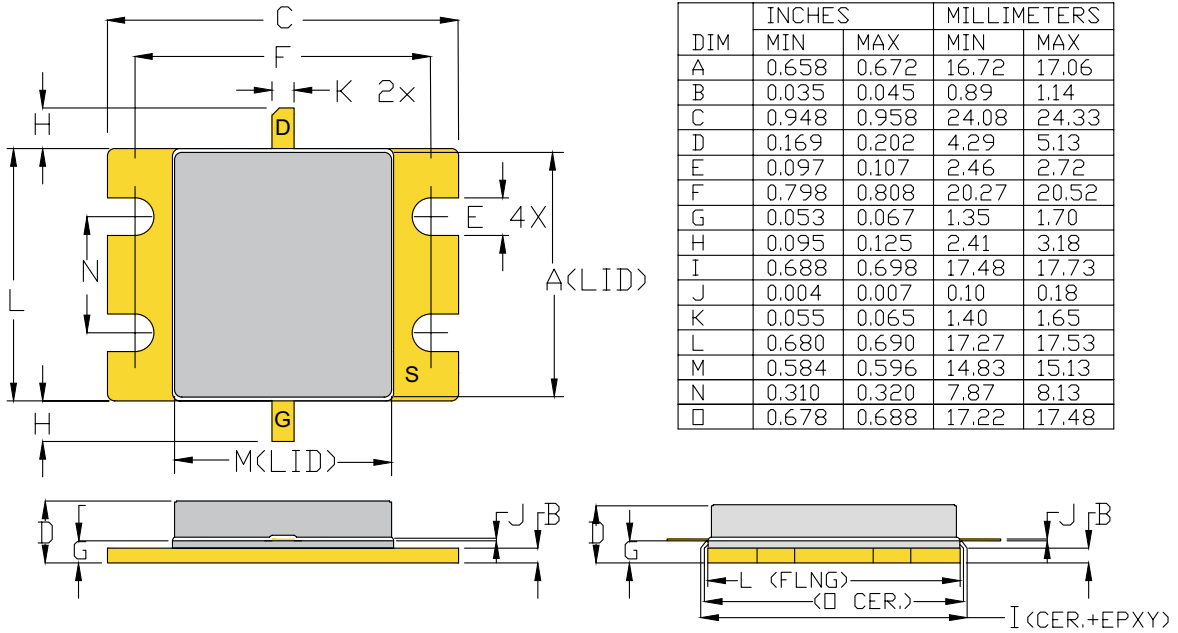
TEST FIXTURE



Bill of Materials for IGT2731L120 Test Fixture

Designator	Description	Quantity	Part Number
C1, C4, C10	CAP 0.1 μ F, 0805, 100V	3	C0805C104K1RAL
C2	CAP 47 μ F, 25V	1	PCV1E470MCL2GS
C3, C11	CAP 1 μ F, 1206, 100V, X7R	2	GRM31CR72A105KA01L
C5	CAP, 39pF, 0805 250V	1	ATC600F390
C6, C9	CAP 5.6pF, +/-0.25, 0805, 250V, Edge Mount	2	ATC600F5R6CT
C7, C8	CAP 12pF, +/-5%, 0805, 250V	2	ATC600F120CT
C12	CAP 68 μ F, 20%, 63V	1	EEE-FK1J680P
L1	IND FB 120 Ω , 0805, 5A	1	ILHB0805ER121V
L3, L4	IND FB 33 Ω @100MHz, 1206, 6A	2	BLM31PG330S
L5, L6	IND 22nH, 0908	2	0908SQ-22NGL
R1, R2	RES 100 Ω , 0805	2	
R3	RES 470 Ω , 0805	1	
PC Board	DK=3.5, 30 mils, 1oz/1oz Copper	2	RF-35TC-0300-C1/C1

PACKAGE PM67A1



**BOLT-DOWN FLANGE and EARLESS FLANGE OPTIONS
 IGT2731L120**

ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivity Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DEFINITIONS:

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.